

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

Claims 1-9 (Canceled).

10. (New) A method for producing a single crystal by Czochralski method with pulling a seed crystal from a raw material melt, wherein when a pulling rate of pulling a single crystal is defined as V (mm/min), a temperature gradient at a solid-liquid interface is defined as G (K/mm) and a highest temperature at an interface between a crucible and a raw material melt is defined as T_{max} (°C), at least, a range of a value of V/G ($\text{mm}^2/\text{K} \cdot \text{min}$) including a desired defect region and/or a desired defect-free region is determined according to the T_{max} (°C), and the single crystal is pulled with controlling a value of V/G ($\text{mm}^2/\text{K} \cdot \text{min}$) within the determined range.

11. (New) The method for producing a single crystal according to Claim 10, wherein the single crystal is pulled with controlling the value of V/G ($\text{mm}^2/\text{K} \cdot \text{min}$) in a range from $-0.000724 \times T_{max} + 1.31$ to less than $-0.000724 \times T_{max} + 1.38$.

12. (New) The method for producing a single crystal according to Claim 10, wherein the single crystal is pulled with controlling the value of V/G ($\text{mm}^2/\text{K} \cdot \text{min}$) in a range of $-0.000724 \times T_{max} + 1.38$ or more.

13. (New) The method for producing a single crystal according to Claim 10, wherein the single crystal is pulled with controlling the value of V/G ($\text{mm}^2/\text{K} \cdot \text{min}$) in a range from $-$

$0.000724 \times T_{\max} + 1.31$ to $-0.000724 \times T_{\max} + 1.35$.

14. (New) The method for producing a single crystal according to Claim 10, wherein the single crystal is pulled with the T_{\max} (°C) being in a range of 1560 °C or less.

15. (New) The method for producing a single crystal according to Claim 11, wherein the single crystal is pulled with the T_{\max} (°C) being in a range of 1560 °C or less.

16. (New) The method for producing a single crystal according to Claim 12, wherein the single crystal is pulled with the T_{\max} (°C) being in a range of 1560 °C or less.

17. (New) The method for producing a single crystal according to Claim 13, wherein the single crystal is pulled with the T_{\max} (°C) being in a range of 1560 °C or less.

18. (New) The method for producing a single crystal according to Claim 10, wherein, at least, the T_{\max} (°C) is changed by providing a heat insulating material between the crucible containing the raw material melt and a heater provided so as to surround the crucible, or by providing a heat insulating material below the crucible.

19. (New) The method for producing a single crystal according to Claim 11, wherein, at least, the T_{\max} (°C) is changed by providing a heat insulating material between the crucible containing the raw material melt and a heater provided so as to surround the crucible, or by providing a heat insulating material below the crucible.

20. (New) The method for producing a single crystal according to Claim 12, wherein, at

least, the T_{\max} ($^{\circ}\text{C}$) is changed by providing a heat insulating material between the crucible containing the raw material melt and a heater provided so as to surround the crucible, or by providing a heat insulating material below the crucible.

21. (New) The method for producing a single crystal according to Claim 13, wherein, at least, the T_{\max} ($^{\circ}\text{C}$) is changed by providing a heat insulating material between the crucible containing the raw material melt and a heater provided so as to surround the crucible, or by providing a heat insulating material below the crucible.

22. (New) The method for producing a single crystal according to Claim 14, wherein, at least, the T_{\max} ($^{\circ}\text{C}$) is changed by providing a heat insulating material between the crucible containing the raw material melt and a heater provided so as to surround the crucible, or by providing a heat insulating material below the crucible.

23. (New) The method for producing a single crystal according to Claim 15, wherein, at least, the T_{\max} ($^{\circ}\text{C}$) is changed by providing a heat insulating material between the crucible containing the raw material melt and a heater provided so as to surround the crucible, or by providing a heat insulating material below the crucible.

24. (New) The method for producing a single crystal according to Claim 16, wherein, at least, the T_{\max} ($^{\circ}\text{C}$) is changed by providing a heat insulating material between the crucible containing the raw material melt and a heater provided so as to surround the crucible, or by providing a heat insulating material below the crucible.

25. (New) The method for producing a single crystal according to Claim 17, wherein, at

least, the T_{\max} ($^{\circ}\text{C}$) is changed by providing a heat insulating material between the crucible containing the raw material melt and a heater provided so as to surround the crucible, or by providing a heat insulating material below the crucible.

26. (New) The method of producing a single crystal according to Claim 10, wherein a silicon single crystal is pulled as the single crystal.

27. (New) The method of producing a single crystal according to Claim 10, wherein a single crystal with a diameter of 200mm or more is pulled as the single crystal.

28. (New) A single crystal produced by the method according to Claim 10.